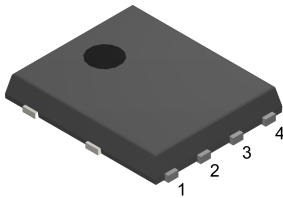
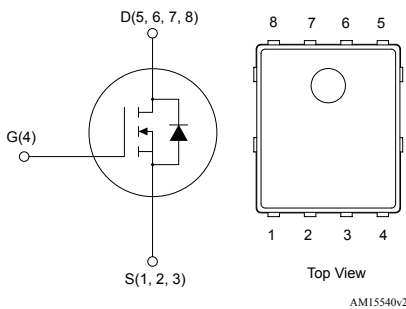


N-channel 40 V, 1.3 mΩ typ., 120 A STripFET F7 Power MOSFET in a PowerFLAT 5x6 package


PowerFLAT 5x6


Features

Order code	V_{DS}	$R_{DS(on)}$ max.	I_D
STL210N4F7	40 V	1.6 mΩ	120 A

- Among the lowest $R_{DS(on)}$ on the market
- Excellent FoM (figure of merit)
- Low C_{rSS}/C_{iSS} ratio for EMI immunity
- High avalanche ruggedness

Applications

- Switching applications

Description

This N-channel Power MOSFET utilizes STripFET F7 technology with an enhanced trench gate structure that results in very low on-state resistance, while also reducing internal capacitance and gate charge for faster and more efficient switching.



Product status link

[STL210N4F7](#)

Product summary

Order code	STL210N4F7
Marking	210N4
Package	PowerFLAT 5x6
Packing	Tape and reel

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	40	V
V_{GS}	Gate-source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	120	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	120	A
$I_{DM}^{(2)(1)}$	Drain current (pulsed)	480	A
P_{TOT}	Total power dissipation at $T_C = 25\text{ }^\circ\text{C}$	150	W
I_{AV}	Avalanche current, repetitive or not repetitive (pulse width limited by maximum junction temperature)	40	A
E_{AS}	Single pulse avalanche energy ($T_j = 25\text{ }^\circ\text{C}$, $I_D = I_{AV}$, $V_{DD} = 25\text{ V}$)	300	mJ
T_j	Operating junction temperature range	-55 to 175	$^\circ\text{C}$
T_{stg}	Storage temperature range		

1. Drain current is limited by package, the current capability of the silicon is 229 A at 25 °C.
2. Pulse width limited by safe operating area

Table 2. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb max.	31.3	$^\circ\text{C/W}$
$R_{thj-case}$	Thermal resistance junction-case max.	1.0	$^\circ\text{C/W}$

1. When mounted on FR-4 board of 1 inch², 2oz Cu, $t < 10\text{ sec}$

2 Electrical characteristics

($T_C = 25\text{ }^\circ\text{C}$ unless otherwise specified)

Table 3. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$	40			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$ $V_{DS} = 40\text{ V}$			1	μA
I_{GSS}	Gate-body leakage current	$V_{GS} = 20\text{ V}$, $V_{DS} = 0\text{ V}$			100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2		4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 16\text{ A}$		1.3	1.6	m Ω

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0\text{ V}$	-	3600	-	pF
C_{oss}	Output capacitance		-	1240	-	pF
C_{riss}	Reverse transfer capacitance		-	88	-	pF
Q_g	Total gate charge	$V_{DD} = 20\text{ V}$, $I_D = 40\text{ A}$, $V_{GS} = 10\text{ V}$ (see Figure 13. Test circuit for gate charge behavior)	-	43	-	nC
Q_{gs}	Gate-source charge		-	19	-	nC
Q_{gd}	Gate-drain charge		-	13	-	nC

Table 5. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 20\text{ V}$, $I_D = 20\text{ A}$, $R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$ (see Figure 12. Test circuit for resistive load switching times and Figure 17. Switching time waveform)	-	16	-	ns
t_r	Rise time		-	10	-	ns
$t_{d(off)}$	Turn-off delay time		-	34	-	ns
t_f	Fall time		-	12	-	ns

Table 6. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{SD}^{(1)}$	Forward on voltage	$I_{SD} = 40\text{ A}$, $V_{GS} = 0\text{ V}$	-		1.2	V
t_{rr}	Reverse recovery time	(see)Figure 14. Test circuit for inductive load switching and diode recovery times $I_D = 40\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 32\text{ V}$	-	53		ns
Q_{rr}	Reverse recovery charge		-	71		nC
I_{RRM}	Reverse recovery current		-	2.7		A

1. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

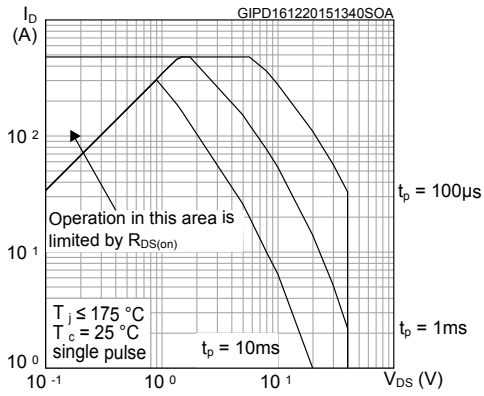


Figure 2. Thermal impedance

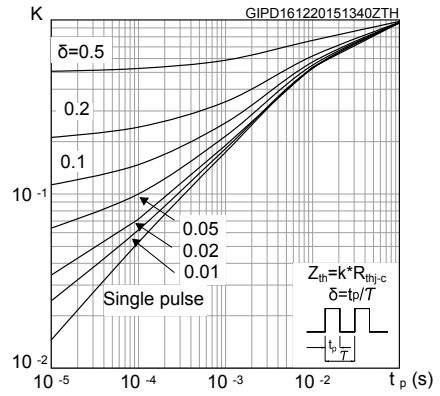


Figure 3. Output characteristics

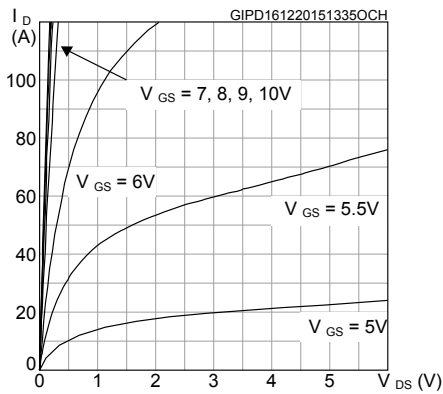


Figure 4. Transfer characteristics

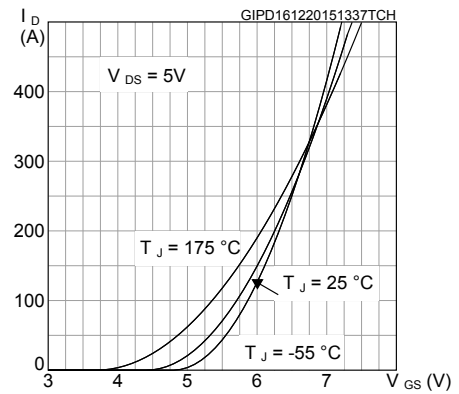


Figure 5. Gate charge vs gate-source voltage

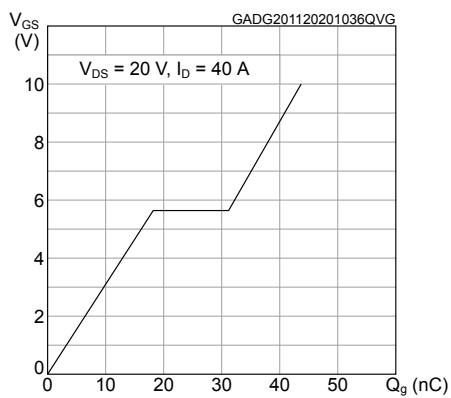


Figure 6. Static drain-source on-resistance

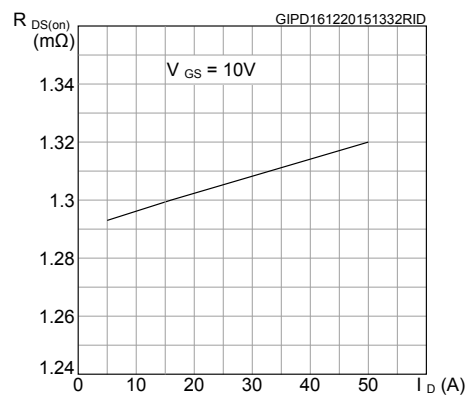


Figure 7. Capacitance variations

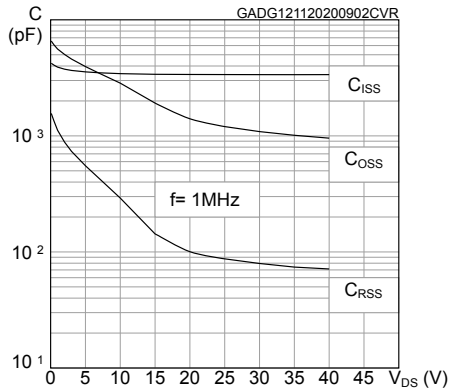


Figure 8. Normalized on-resistance vs temperature

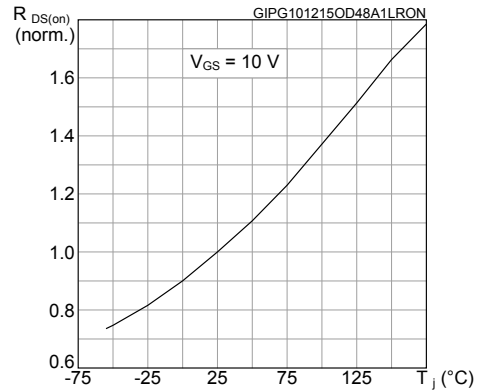


Figure 9. Normalized $V_{(BR)DSS}$ vs temperature

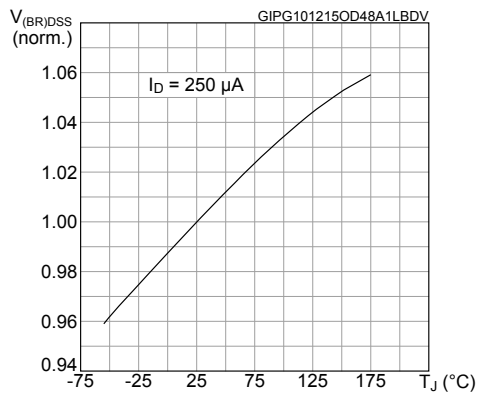


Figure 10. Normalized gate threshold voltage vs temperature

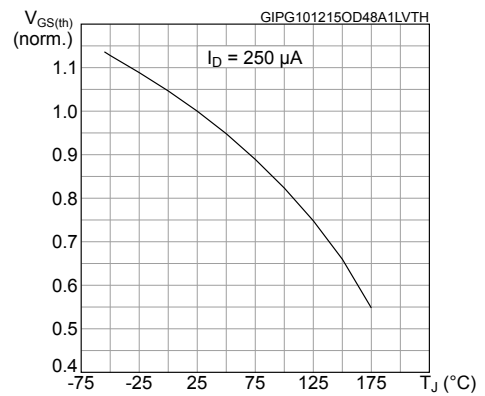
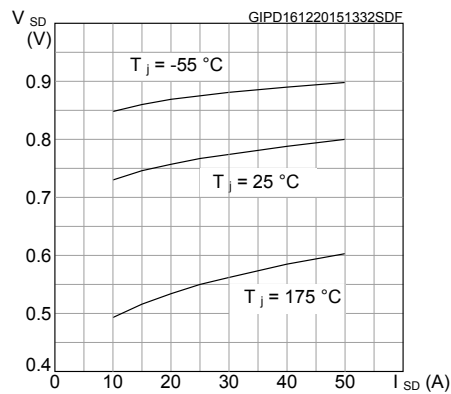
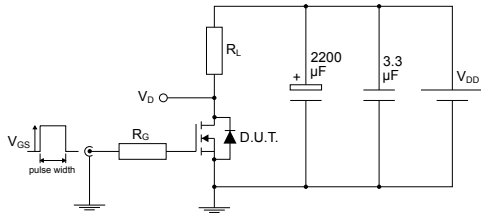


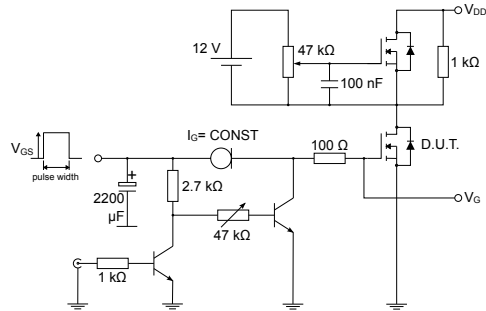
Figure 11. Source-drain diode forward characteristics



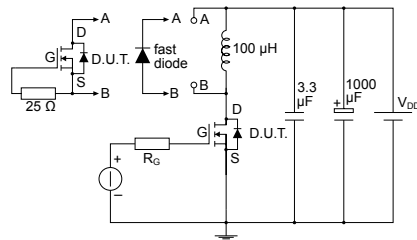
3 Test circuits

Figure 12. Test circuit for resistive load switching times


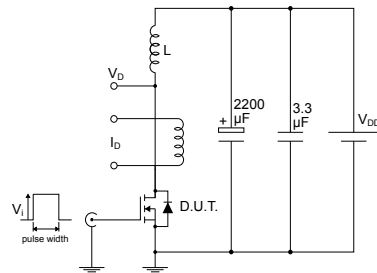
AM01468v1

Figure 13. Test circuit for gate charge behavior


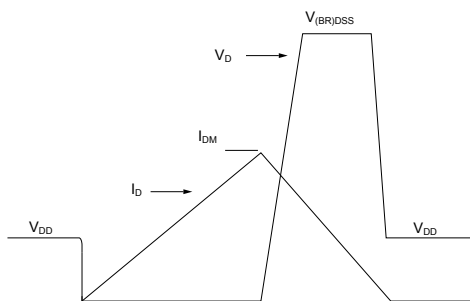
AM01469v1

Figure 14. Test circuit for inductive load switching and diode recovery times


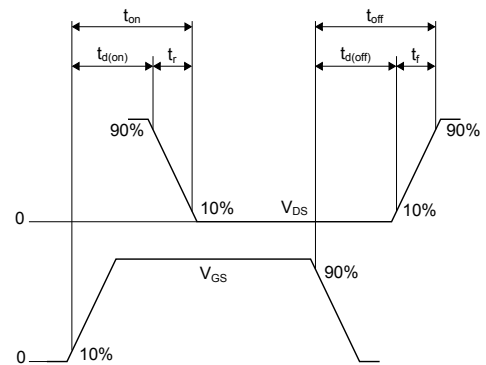
AM01470v1

Figure 15. Unclamped inductive load test circuit


AM01471v1

Figure 16. Unclamped inductive waveform


AM01472v1

Figure 17. Switching time waveform


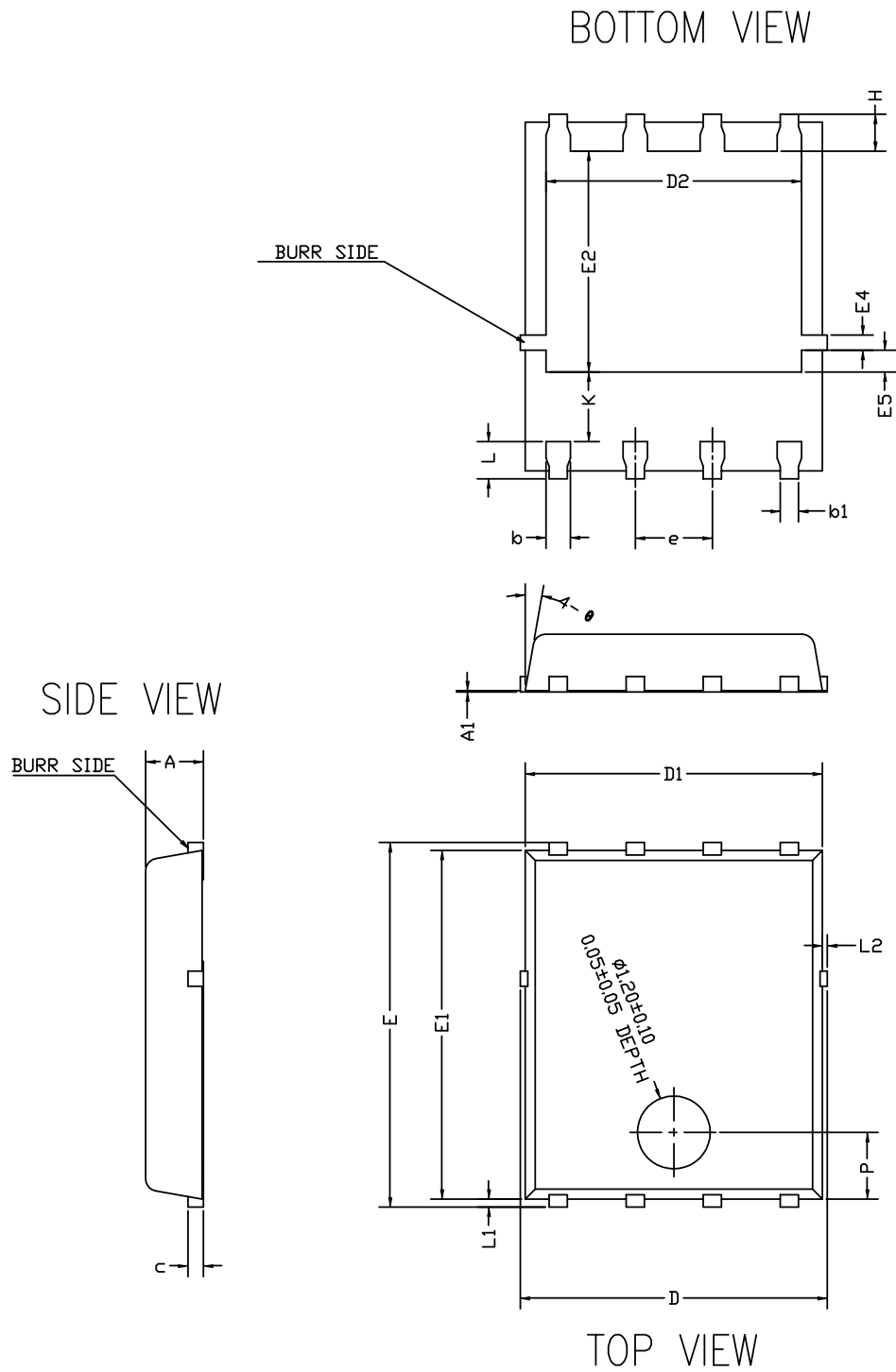
AM01473v1

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 PowerFLAT 5x6 type SUBCON package information

Figure 18. PowerFLAT 5x6 type SUBCON package outline

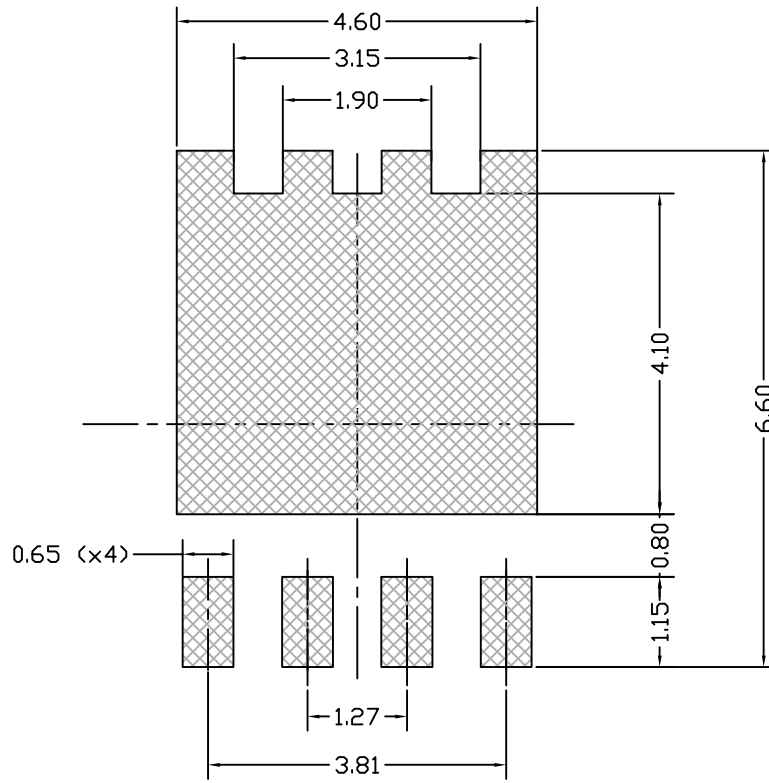


8231817_SUBCON_REV4

Table 7. PowerFLAT 5x6 type SUBCON package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.90	0.95	1.00
A1		0.02	
b	0.35	0.40	0.45
b1		0.30	
c	0.21	0.25	0.34
D	4.80		5.10
D1	4.80	4.90	5.00
D2	4.01	4.21	4.31
e	1.17	1.27	1.37
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.54	3.64	3.74
E4	0.15	0.25	0.35
E5	0.26	0.36	0.46
H	0.51	0.61	0.71
K	0.95		
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
L2			0.10
P	1.00	1.10	1.20
θ	8°	10°	12°

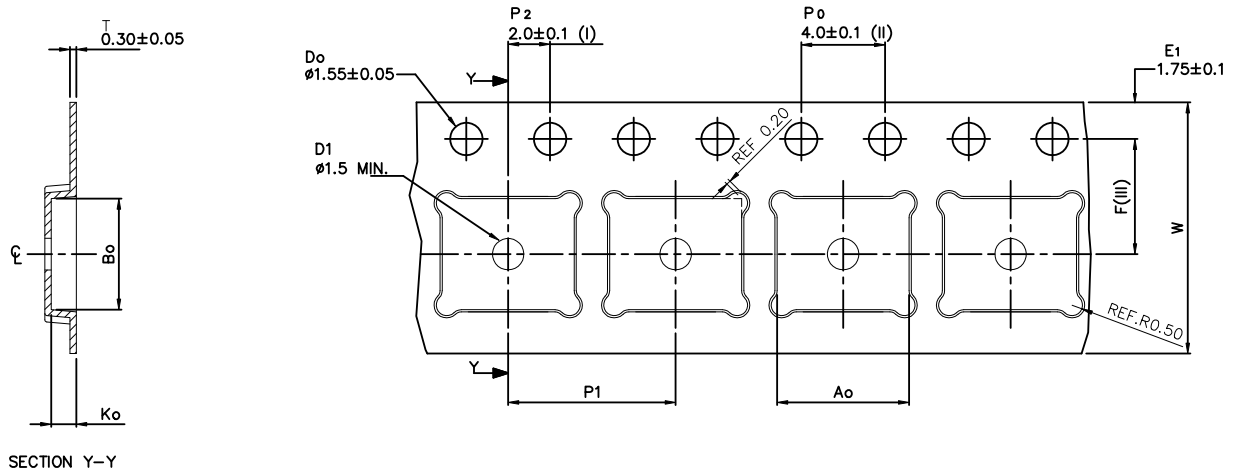
Figure 19. PowerFLAT 5x6 recommended footprint (dimensions are in mm)



8231817_FOOTPRINT_simp_Rev_20

4.2 PowerFLAT 5x6 packing information

Figure 20. PowerFLAT 5x6 tape (dimensions are in mm)



A ₀	6.30 +/− 0.1
B ₀	5.30 +/− 0.1
K ₀	1.20 +/− 0.1
F	5.50 +/− 0.1
P ₁	8.00 +/− 0.1
W	12.00 +/− 0.3

(I) Measured from centreline of sprocket hole to centreline of pocket.

(II) Cumulative tolerance of 10 sprocket holes is ± 0.20 .

(III) Measured from centreline of sprocket hole to centreline of pocket

Base and bulk quantity 3000 pcs
All dimensions are in millimeters

8234350_Tape_rev_C

Figure 21. PowerFLAT 5x6 package orientation in carrier tape

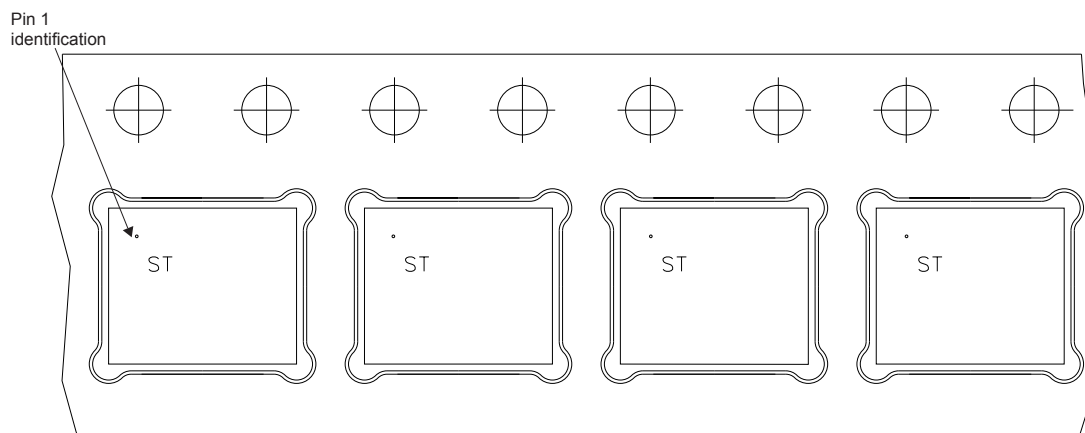
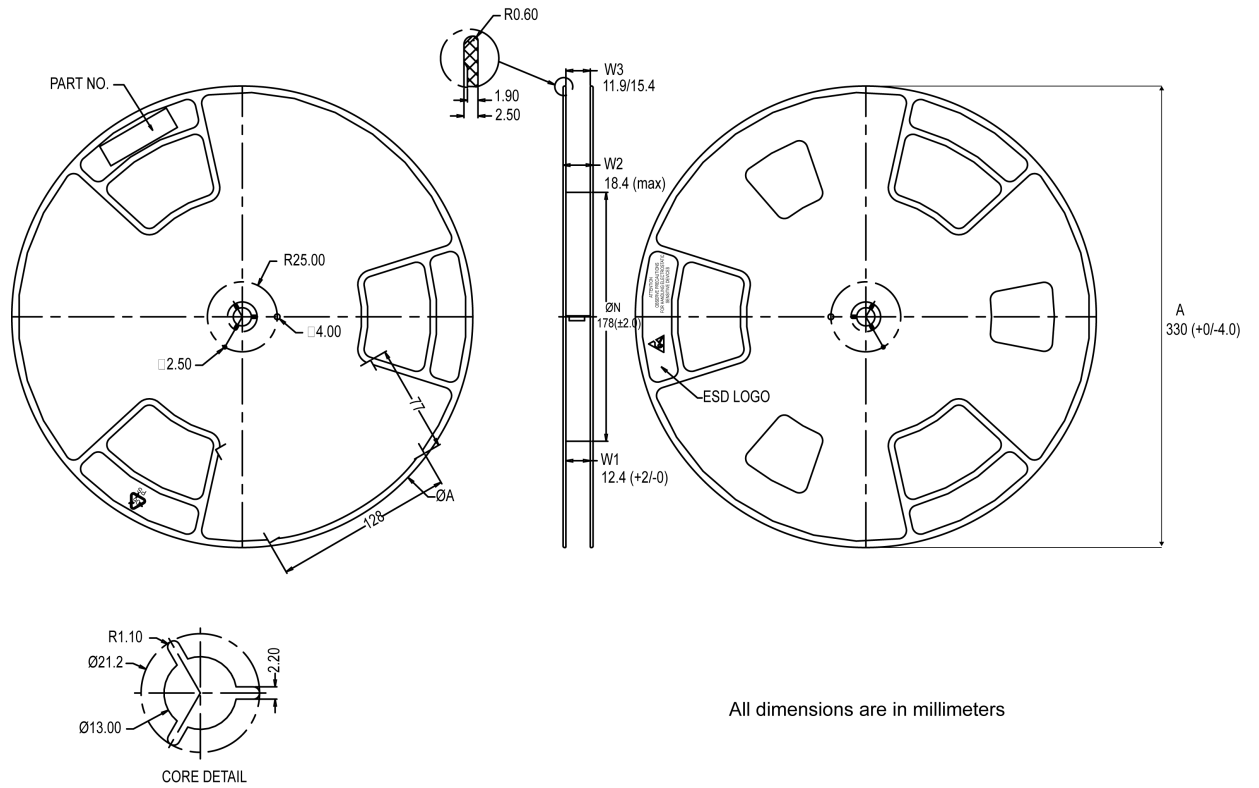


Figure 22. PowerFLAT 5x6 reel

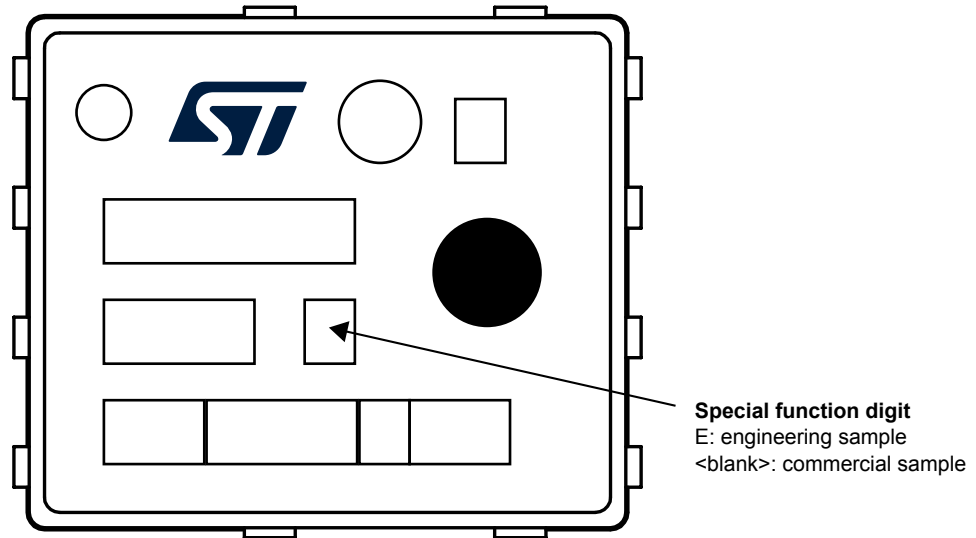


All dimensions are in millimeters

8234350_Reel_rev_C

4.3 PowerFLAT 5x6 marking information

Figure 23. PowerFLAT 5x6 marking information



Note: *Engineering Samples: these samples can be clearly identified by a dedicated special symbol in the marking of each unit. These samples are intended to be used for electrical compatibility evaluation only; usage for any other purpose may be agreed only upon written authorization by ST. ST is not liable for any customer usage in production and/or in reliability qualification trials.*

Commercial Samples: fully qualified parts from ST standard production with no usage restrictions.

Revision history

Table 8. Document revision history

Date	Version	Changes
13-Oct-2020	1	Initial release.
20-Nov-2020	2	Updated Section 2 Electrical characteristics, Figure 7. Capacitance variations and Figure 5. Gate charge vs gate-source voltage.

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